Pri rity Appl. N . 09/332,271

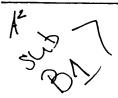
In th Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 C.F.R. § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

CLAIMS

Please cancel claims 1-20.



- 21. A conductive line comprising:
- a polysilicon layer; and

a metal-silicide layer against the layer of polysilicon, the metal-silicide layer comprising a Group III dopant or a Group // dopant.

- 22. The conductive line of claim 21 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1 x 10¹⁸ ions/cm³.
- 23. A metal-silicide layer comprising a Group III dopant or a Group V dopant.
- 24. The metal-silicide of claim 23 comprising a concentration of the dopant of at least about 1 \times 10¹⁸ ions/cm³.

- 25. A programmable-read-only-memory device comprising:
- a first dielectric layer over a substrate,
- a floating gate over the first dielectric layer;
- a second dielectric layer over the floating gate;
- a conductive line over the second dielectric layer; and
- a metal-silicide layer over the conductive line, the metal-silicide layer comprising a Group III dopant or a Group V dopant.
- 26. The programmable-read-only-memory device of claim 25 wherein the device is an EPROM.
- 27. The programmable-read-only-memory device of claim 25 wherein the device is an EEPROM.
- 28. The programmable-read-only-memory device of claim 25 wherein the metal-silicide ayer comprises a concentration of the dopant of at least about 1 x 10¹⁸ ions/cm³.